

United States Patent and Trademark Office

W

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	. FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/807,304	03/24/2004	Toshimitsu Kariya	03500.017974 3813	
••••	7590 12/31/200 CELLA HARPER &	EXAMINER		
30 ROCKEFEI		BARTON, JEFFREY THOMAS		
NEW YURK, I	NEW YORK, NY 10112		ART UNIT	PAPER NUMBER
			1795	
			MAIL DATE	DELIVERY MODE
			12/31/2007	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

		Application No.	Applicant(s)	
Office Action Summary		10/807,304	KARIYA, TOSHIMITSU	
		Examiner	Art Unit	
		Jeffrey T. Barton	1795	
The MAILING DATE of Period for Reply	this communication app	ears on the cover sheet with the c	orrespondence address	
WHICHEVER IS LONGER, F - Extensions of time may be available u after SIX (6) MONTHS from the mailin - If NO period for reply is specified abov - Failure to reply within the set or extend	FROM THE MAILING DA nder the provisions of 37 CFR 1.13 g date of this communication. e, the maximum statutory period w ded period for reply will, by statute, than three months after the mailing	IS SET TO EXPIRE 3 MONTH(ATE OF THIS COMMUNICATION 6(a). In no event, however, may a reply be time ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONEI date of this communication, even if timely filed	N. nely filed the mailing date of this communication. D (35 U.S.C. § 133).	
Status				
	2b)⊠ This s in condition for allowan	ctober 2007. action is non-final. ce except for formal matters, pro x parte Quayle, 1935 C.D. 11, 45		
Disposition of Claims				
4) ⊠ Claim(s) <u>1-5</u> is/are pen 4a) Of the above claim(5) □ Claim(s) is/are a 6) ⊠ Claim(s) <u>1-3</u> is/are reje 7) □ Claim(s) is/are of 8) □ Claim(s) are sub	s) <u>4 and 5</u> is/are withdra allowed. cted. objected to.			
Application Papers				
Applicant may not reques Replacement drawing sho	is/are: a) acce t that any objection to the c eet(s) including the correcti	epted or b) objected to by the Edrawing(s) be held in abeyance. See on is required if the drawing(s) is objection.	e 37 CFR 1.85(a). ected to. See 37 CFR 1.121(d).	
Priority under 35 U.S.C. § 119				
 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 				
Attachment(s) 1) Notice of References Cited (PTO-2) Notice of Draftsperson's Patent Dr 3) Information Disclosure Statement(Paper No(s)/Mail Date 20040831.	awing Review (PTO-948) s) (PTO/SB/08)	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal Pa	ite	

Art Unit: 1795

DETAILED ACTION

Election/Restrictions

1. Applicant's election without traverse of Group I, claims 1-3 in the reply filed on 18

October 2007 is acknowledged. Claims 4 and 5 are withdrawn as drawn to a

nonelected invention.

Specification

2. The disclosure is objected to because of the following informalities: throughout the specification, the element "phosphorus" is referred to as "phosphor". Each instance of this should be corrected to recite the correct name of the element.

Appropriate correction is required.

Claim Objections

3. Claim 1 is objected to because of the following informalities: At lines 10 and 11 of the claim the element "phosphorus" is referred to as "phosphor". The claim should be amended to recite the correct name of the element. Appropriate correction is required.

Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

10/807,304 Art Unit: 1795

- 5. The factual inquiries set forth in *Graham* v. *John Deere Co.*, 383 U.S. 1, 148 USPQ 459 (1966), that are applied for establishing a background for determining obviousness under 35 U.S.C. 103(a) are summarized as follows:
 - 1. Determining the scope and contents of the prior art.
 - 2. Ascertaining the differences between the prior art and the claims at issue.
 - 3. Resolving the level of ordinary skill in the pertinent art.
 - 4. Considering objective evidence present in the application indicating obviousness or nonobviousness.
- 6. Claims 1-3 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sano et al (JP 11-243218) in view of Kondo. (US 6,103,138) A machine translation of Sano et al that was relied upon in interpreting Sano et al has been made of record, and is enclosed with this Office Action.

Regarding claims 1 and 2, Sano et al disclose a stacked photovoltaic element comprising a structure (Figure 1) formed by sequentially arranging a metal layer (101), lower transparent conductive layer (102), first n-type microcrystalline silicon layer (103), first i-type microcrystalline silicon layer (105), first p-type non-single crystal silicon layer (107), a second n-type microcrystalline silicon layer (108), a second i-type microcrystalline silicon layer (110), and a second p-type non-single crystal silicon layer (111) on a support body (100). Sano et al further disclose sequentially laying a third n-type non-single crystal silicon layer (112), a third i-layer of amorphous silicon (113), a third p-type non-single crystal silicon layer (114), and upper transparent conductive

10/807,304

Art Unit: 1795

layer of ITO (115) on and in contact with the second p-layer. (Figure 1; Paragraphs 0078-0081; 0091-0148)

Sano et al do not explicitly disclose the first and second i-type layers containing phosphorus, such that the content ratio of P:Si of the first i-type layer is greater than that of the second i-type layer.

Kondo et al teaches single and tandem photovoltaic cells formed from p-i-n junctions having microcrystalline i-type layers (Figures 1 and 4; microcrystalline i-type layer 102b; Column 7, lines 23-30), wherein the i-type layer(s) comprise phosphorus at levels of 1 ppm or more, with examples provided at 3 ppm (Table 2; Column 9, lines 29-42) In addition, Kondo et al teach that it is preferred that the phosphorus is unevenly distributed in the films, with concentration increasing towards the electroconductive substrate 101, which is analogous to the substrate 120 of Figure 1 of Sano et al. This preference is due to the presence of higher grain boundary densities closer to this substrate, allowing the phosphorus atoms to exhibit their favorable effect more efficiently in this region. (Column 4, lines 9-19)

It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the tandem cell of Sano et al by incorporating phosphorus into the i-type microcrystalline layers 105 and 110 at levels of about 3 ppm, as taught by Kondo, because Kondo teaches that providing phosphorus to the layers in this amount allows faster deposition of the cell layers with much less pronounced degradation of photovoltaic properties. (Table 2; Column 9, lines 29-42) The benefits of faster cell production would have been clear to one having ordinary skill in the art.

It would also have been obvious to one having ordinary skill in the art at the time the invention was made to provide a somewhat greater concentration of phosphorus to the first i-type layer (105) than to the second i-type layer (110), because layer 105 lies closer to electroconductive substrate 120 than layer 110, and Kondo teaches that it is preferred to provide a higher phosphorus concentration closer to the electroconductive substrate, because the phosphorus atoms exhibit their favorable effect more efficiently in this region. (Column 4, lines 9-19)

Regarding claim 3, Kondo teaches phosphorus concentrations of at least 1 ppm, with the examples using 3 ppm concentration. (Table 2; Column 9, lines 29-42) Within the combined cell, it would have been obvious to select phosphorus concentrations corresponding to the levels disclosed in Kondo.

Conclusion

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Dr. Jeffrey T. Barton whose telephone number is (571) 272-1307. The examiner can normally be reached on M-F 9:00AM - 5:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nam Nguyen can be reached on (571) 272-1342. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

10/807,304 Art Unit: 1795

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

JTB

21 December 2007

NAM NGWYEN

SUPERVIGORY PATENT EXAMINER TECHNOLOGY CENTER 1700